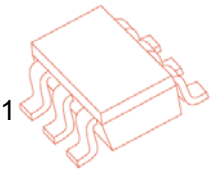
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Transistors

UMX1N General purpose transistors(dual transistors)

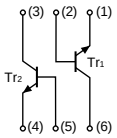
SOT-363



FEATURES

- **Two 2SC2412K chips in a SOT-563 package.**
- **Mounting possible with SOT-563 automatic mounting machines.**
- **Transistor elements are independent, eliminating interference.**
- **Mounting cost and area can be cut in half.**

MARKING:X1



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA,I_C=0	7			V
Collector cut-off current	I_{CBO}	V_{CB}=60V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=7V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=6V,I_C=1mA	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA,I_B=5mA			0.4	V
Transition frequency	f_T	V_{CE}=12V,I_C=2mA,f=100MHz		180		MHz
Collector output capacitance	C_{ob}	V_{CB}=12V,I_E=0,f=1MHz		2.0	3.5	pF